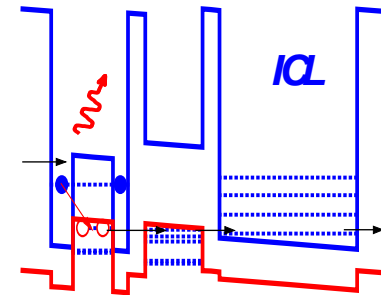
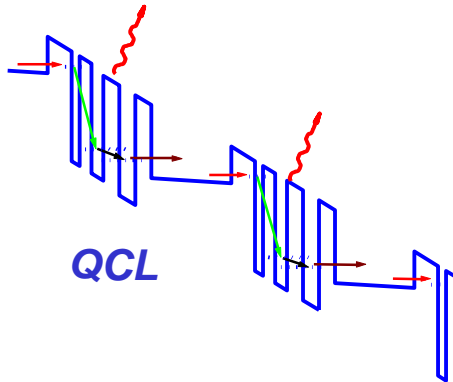


PERFORMANCE TRADE-OFFS: INTERSUBBAND vs. INTERBAND QUANTUM CASCADE LASERS



**International Workshop on Quantum Cascade Lasers
(Sevilla, 5 January 2004)**

J. R. Meyer, I. Vurgaftman, & W. W. Bewley (*Naval Research Laboratory*)

With devices from: Manijeh Razeghi & Steve Slivken (*Northwestern U.*)

**Embedded
Talk:**

**PROGRESS & CHALLENGES IN THE DEVELOPMENT
OF INTERBAND CASCADE LASERS**

R. Q. Yang & C. J. Hill (*JPL*)

Question: Which most promising for high cw powers in mid-IR (3-5 μm)?

Report Documentation Page

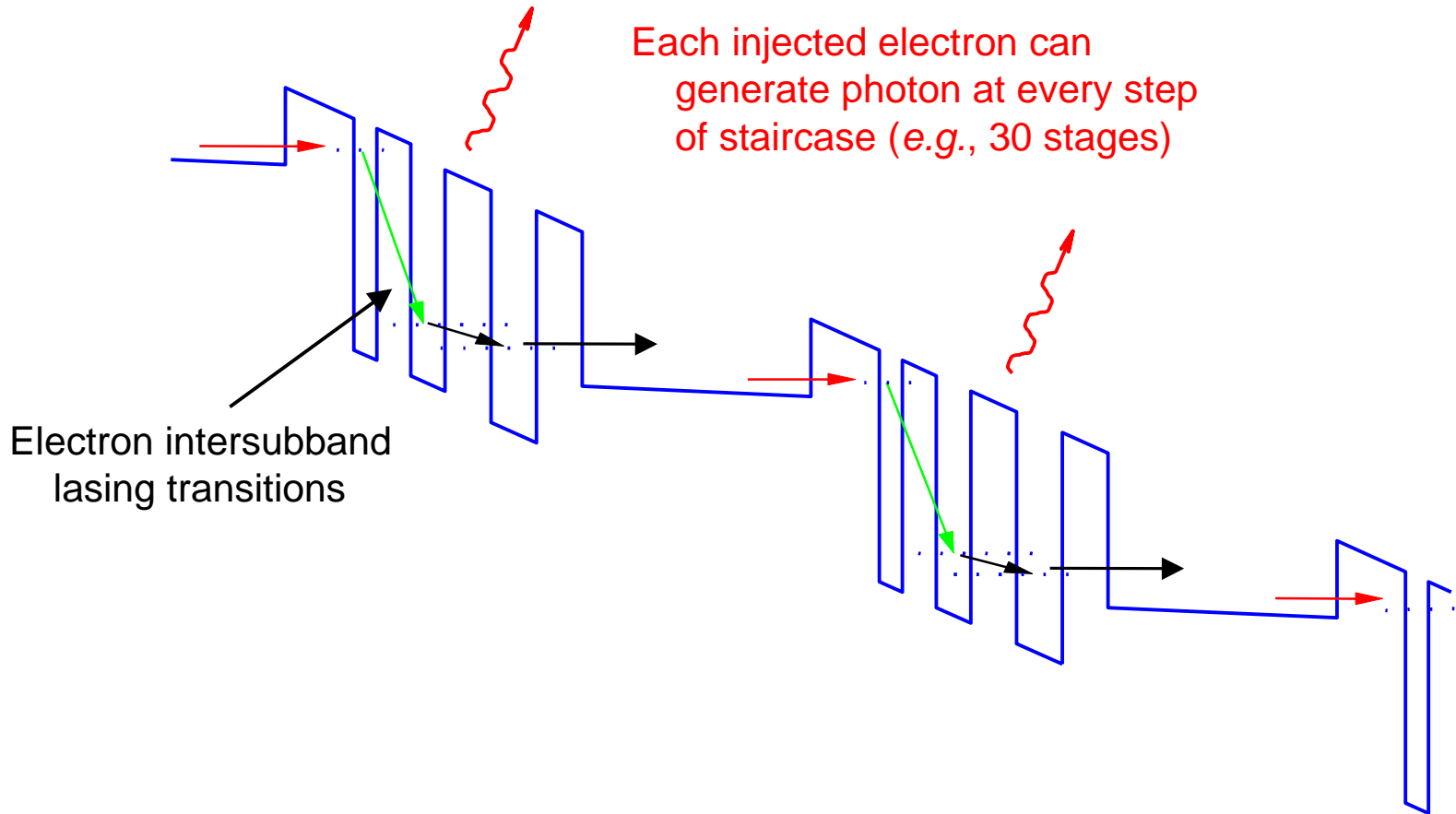
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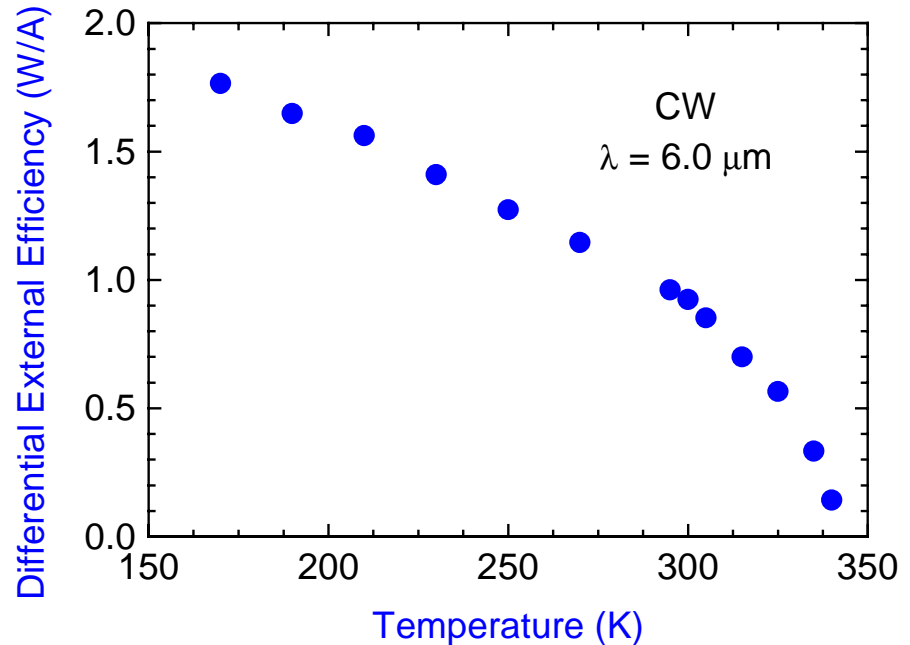
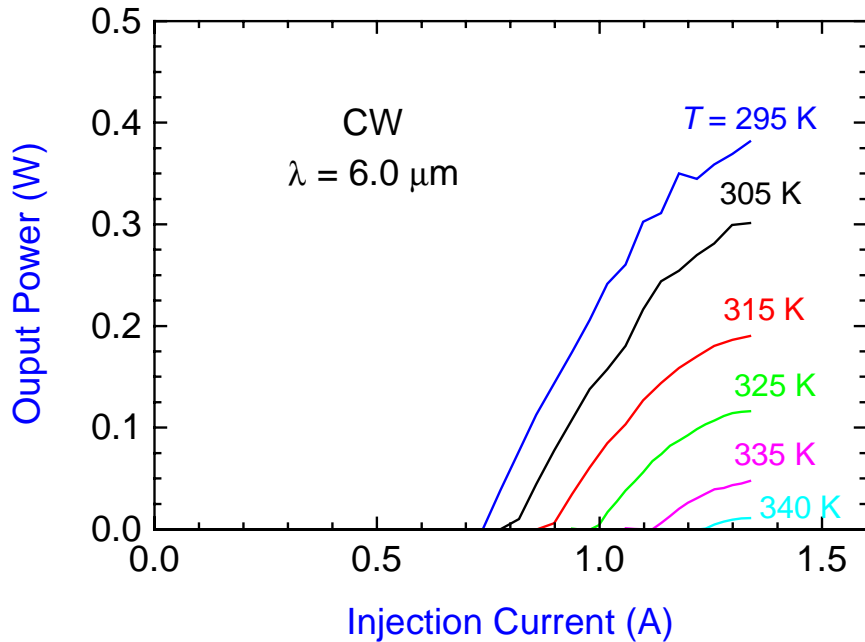
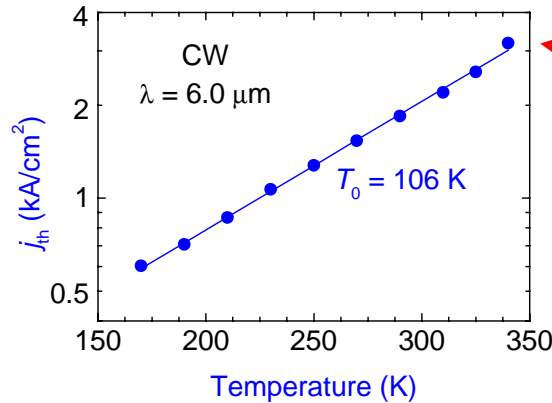
QUANTUM CASCADE LASER (QCL)



- **Advantages:** Multiple stages for high slope efficiency, Small threshold carrier density, Large T_0 , Mature materials (InP/GaAs), Low LEF
- **Disadvantages:** Multiple stages require greater heat dissipation, Short phonon lifetime increases threshold, Strain compensation required to reach $\lambda < 5 \mu\text{m}$



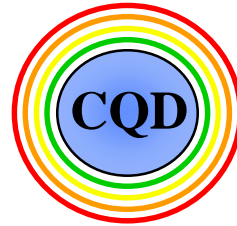
NRL CHARACTERIZATION OF NORTHWESTERN QCLs *(Devices courtesy of M. Razeghi & S. Slivken)*



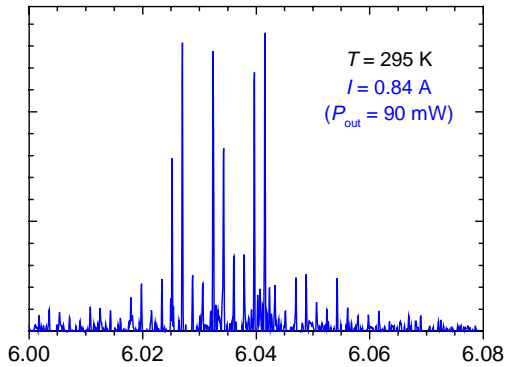
CW $P_{out} = 360 \text{ mW}$ @ 300 K, 110 mW @ 325 K, $\eta_{wall} = 2.7\%$ @ 300 K



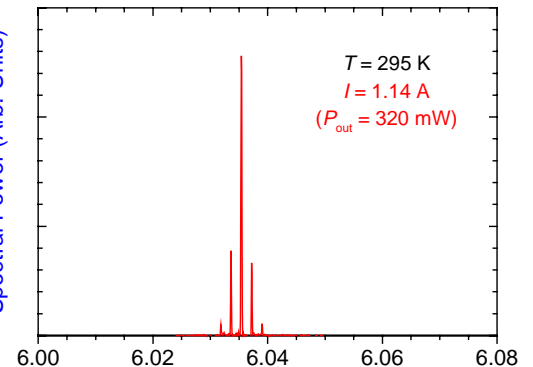
SPECTRA & FAR-FIELD



Spectral Power (Arb. Units)



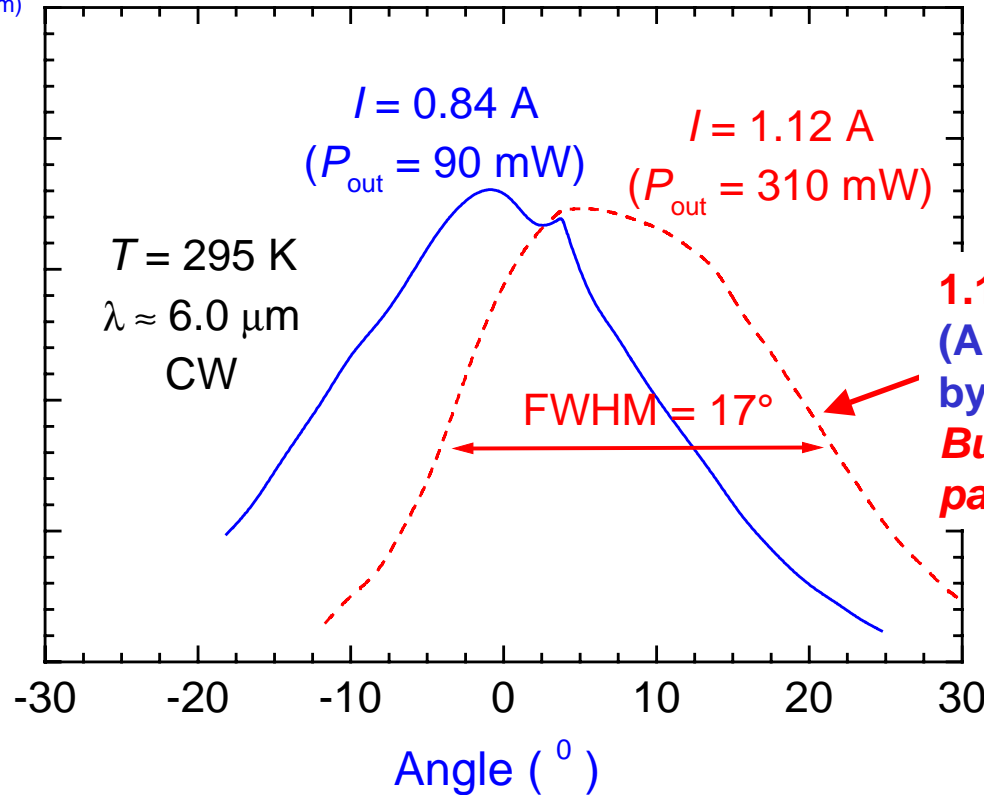
Spectral Power (Arb. Units)



Wavelength (μm)

Wavelength (μm)

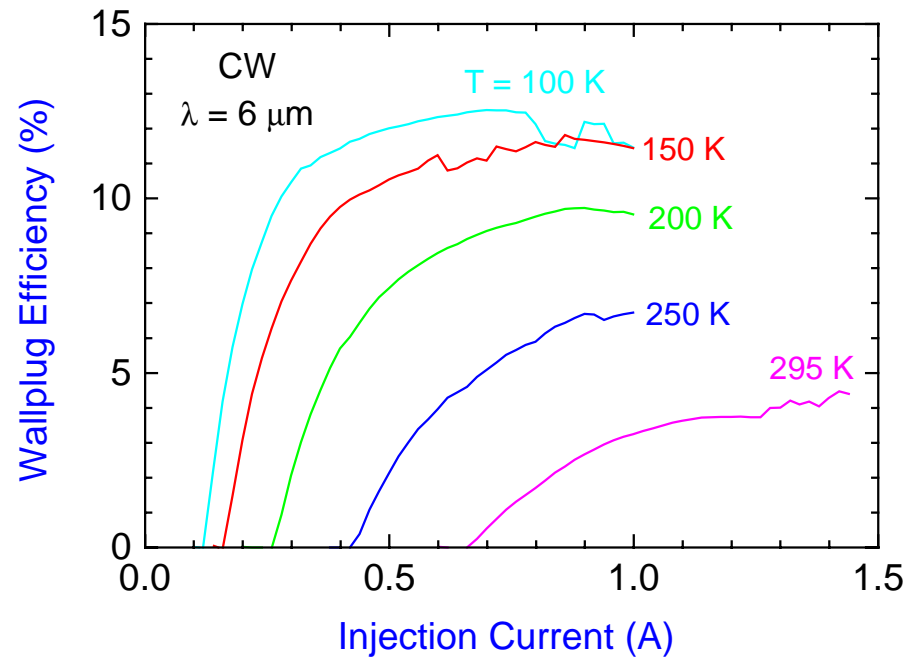
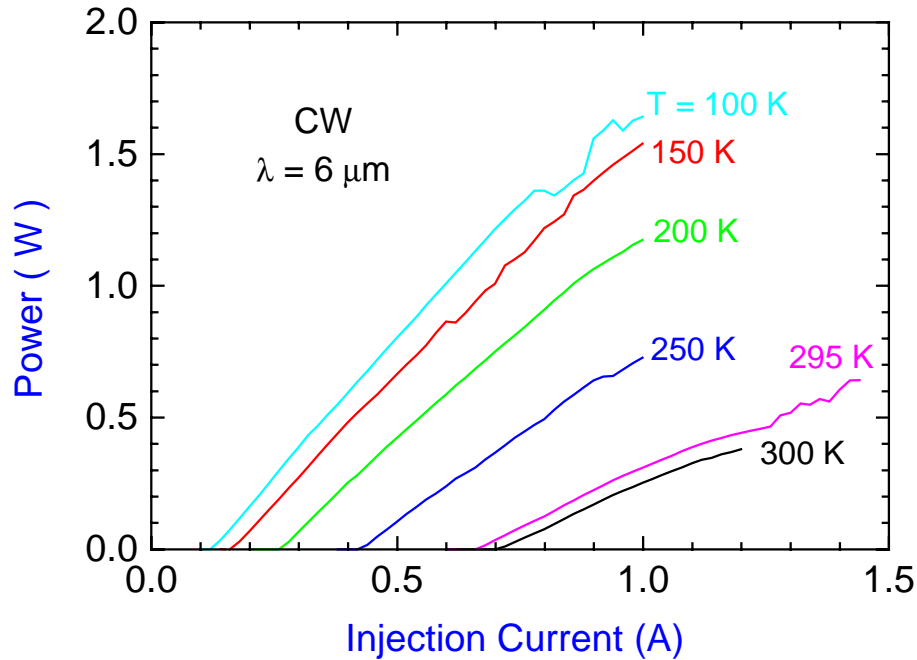
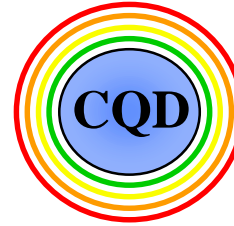
Far-Field Intensity (Arb. Units)



1.14 \times Diffraction Limit
(Assumes index guiding by 13- μm mesa)
But tilt implies at least partial gain-guiding



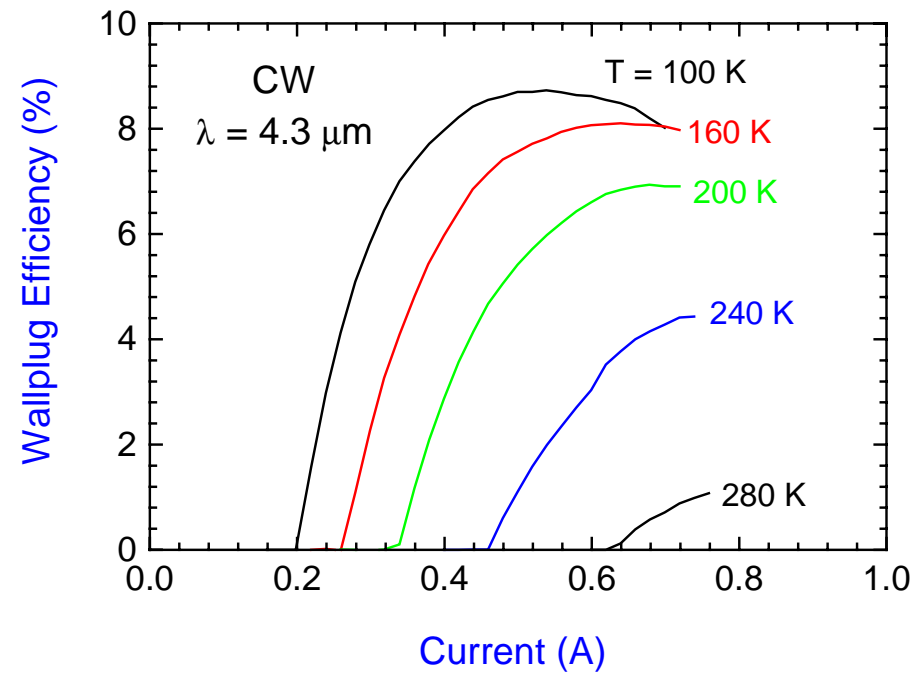
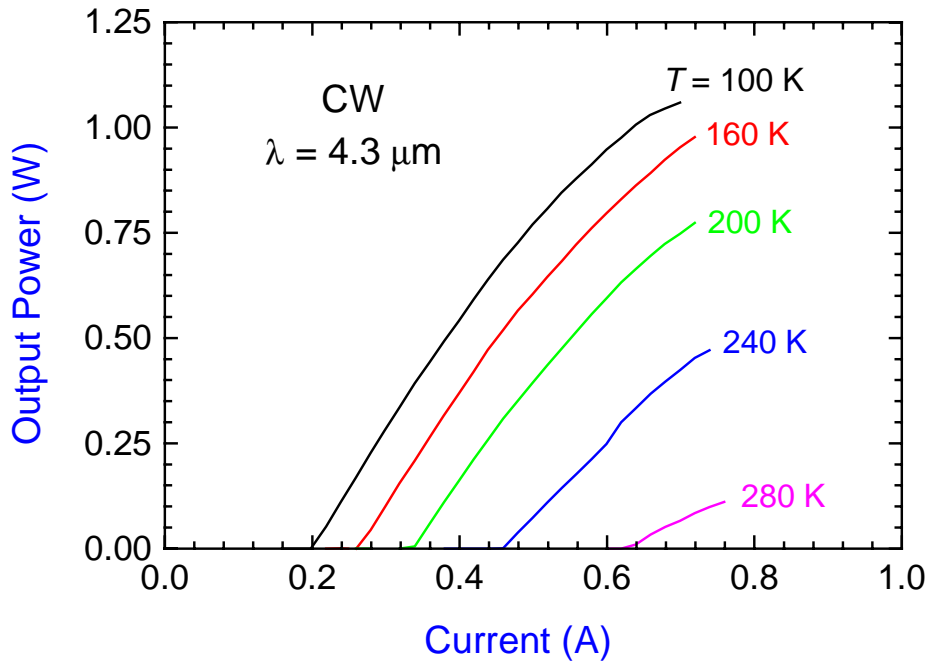
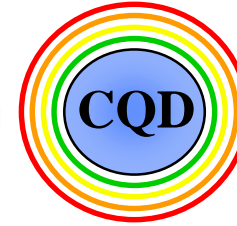
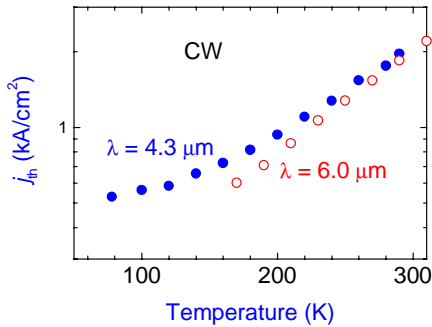
NEW 6 μm LASER



CW $P_{out} > 1.1 \text{ W}$ @ 200 K, 640 mW @ 295 K, $\eta_{wall}(295\text{K}) = 4.5\%$



SHORTEN WAVELENGTH TO $4.3 \mu\text{m}$



CW @ 160 K: $P_{out} \approx 1 \text{ W}$, $\eta_{wall} = 8.1\%$



TYPE-II ANTIMONIDE “W” LASER

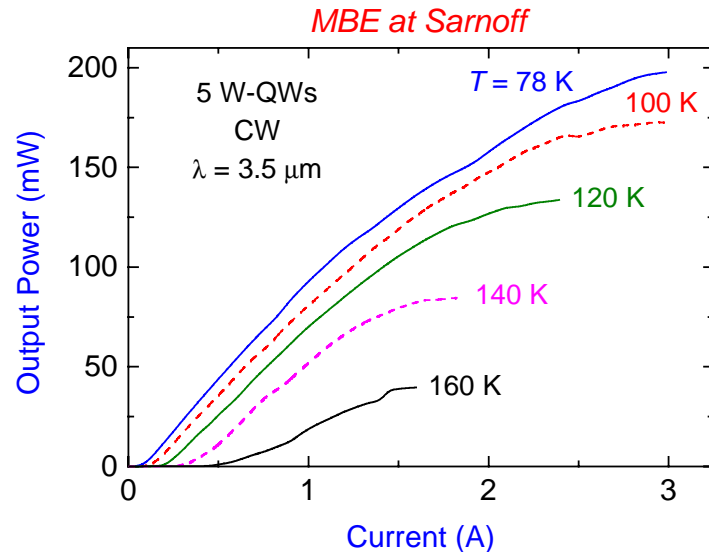
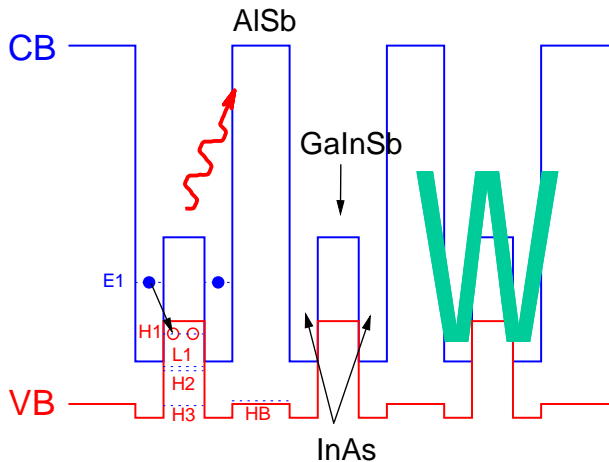
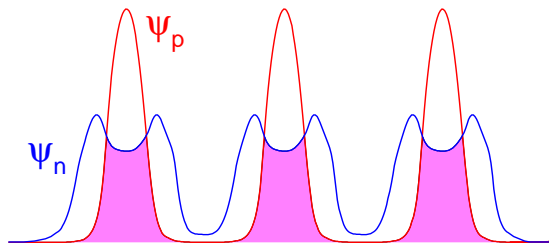
Meyer et al. APL 67, 757 (1995);
U.S. Patent # 5,793,787

Advantages:

- *Vs. type-I diodes*: High differential gain, excellent electrical confinement, Auger suppression
- *Vs. QCL*: Interband relaxation for lower j_{th} , Single stage for lower heat-dissipation threshold

Disadvantages:

- Lower slope efficiency, Immature GaSb-based materials, *Far less optimized*



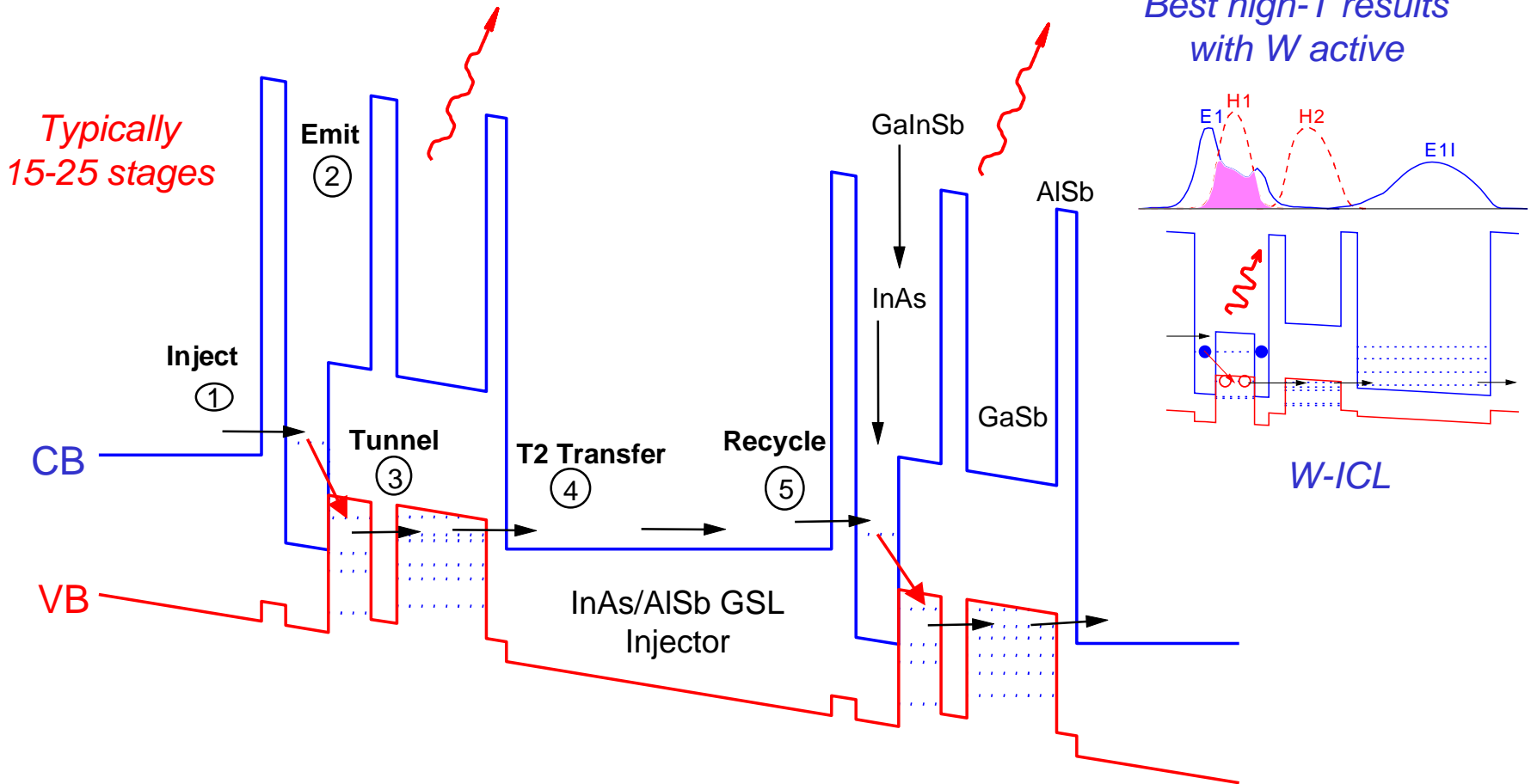
$cw T_{max} = 195 \text{ K}$

$\eta_{wall} = 7.2\% @ 78 \text{ K}, 5.4\% @ 140 \text{ K}$



INTERBAND CASCADE LASER (ICL)

First proposed: *R. Q. Yang, Superlatt. Microstruct. 17, 77 (1995)*



Advantages: High slope efficiency (Multiple stages), Lower threshold (long τ_R)

Disadvantages: Higher heat-dissipation threshold (Multiple stages), GaSb-based



Progress and Challenges in the Development of Interband Cascade Lasers

Rui Q. Yang and Cory J. Hill

**Jet Propulsion Laboratory
California Institute of Technology, Pasadena, CA**

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NASA Enabling Concepts and Technologies Program

JPL Internal Research and Technology Development Program

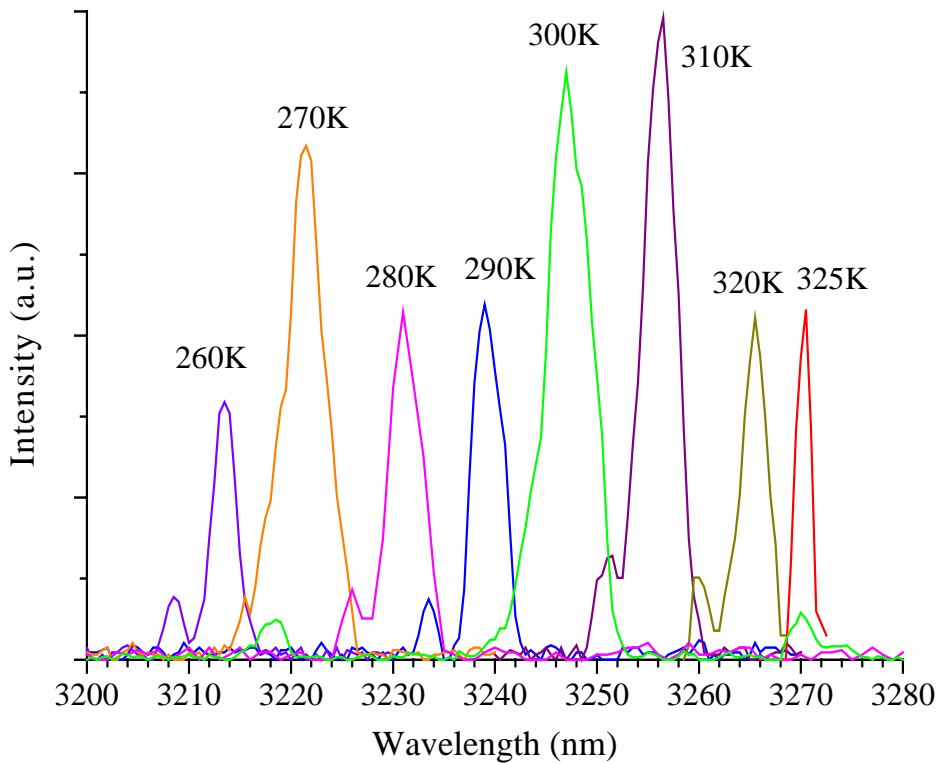
International Workshop on Quantum Cascade Lasers
Seville, Spain, Jan. 4-8, 2004



HIGHER-TEMPERATURE OPERATION

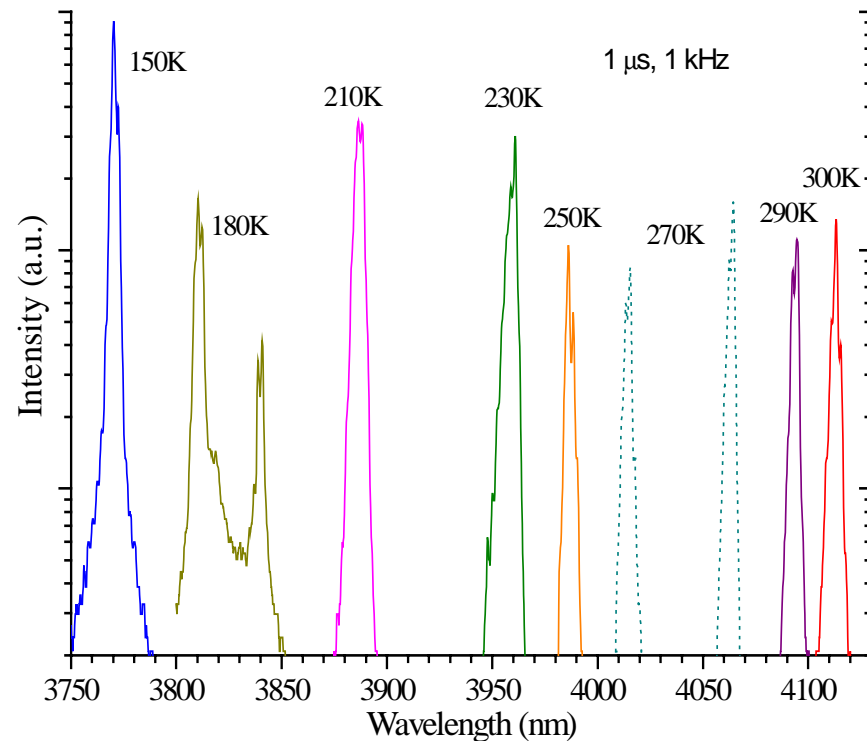


15 stages, 150 μm x 0.8 mm mesa

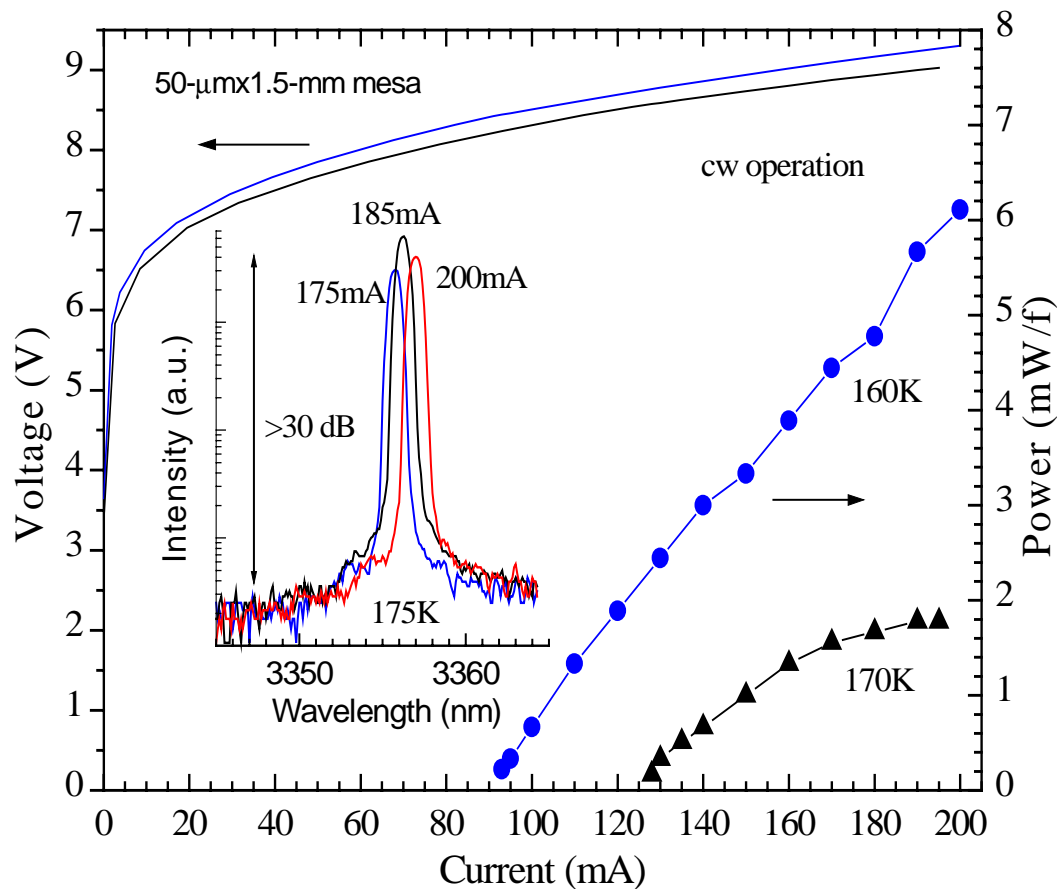


Pulsed lasing at $\lambda = 3.27 \mu\text{m}$ up to 325 K
(Limited by circuit ringing & temperature setting of cryostat)

23-stages, 150- μm x 1-mm mesa



Longest-wavelength III-V interband diode laser operating at room temperature ($\lambda = 4.1 \mu\text{m}$)



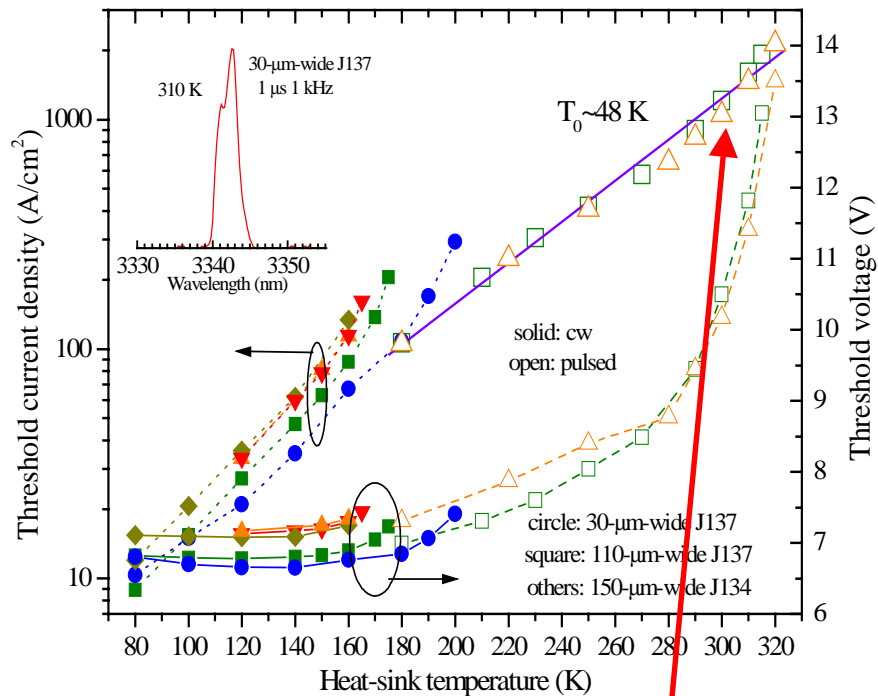
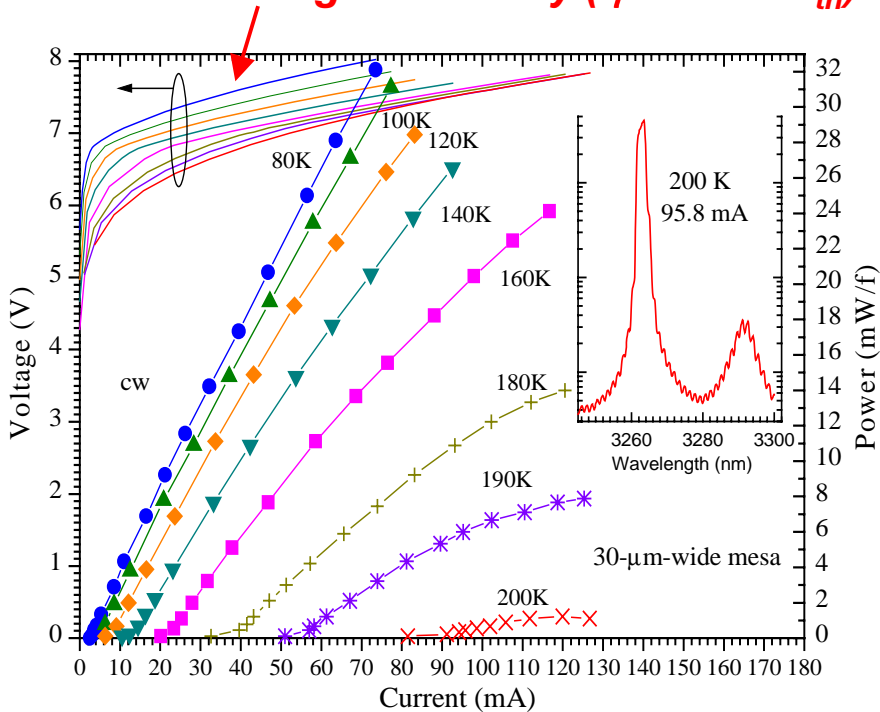
- DFB lasers operated cw up to 175 K in single mode (> 30 dB sidemode suppression)
- Wavelength tunable with current at a rate of ~ 0.05 nm/mA
- Temperature tuning coefficient ~ 0.2 nm/K
- Output power (>1 mW) at 175 K enough for gas sensing



LOW THRESHOLD, HIGH CW T_{max}



Excellent voltage efficiency ($\eta\omega > 0.9eV_{th}$)



J_{th} (200K in cw) ~ 304 A/cm² (30- μ m-wide device)

$R_{sth} \sim 14$ K \cdot cm²/kW (specific thermal resistance)

**$j_{th}(300K) = 1.05$ kA/cm²
(Lower than any QCL)**

If R_{sth} reduced to 2 K \cdot cm²/kW (smaller device size & better package):
theoretical cw $T_{max} \geq 285$ K

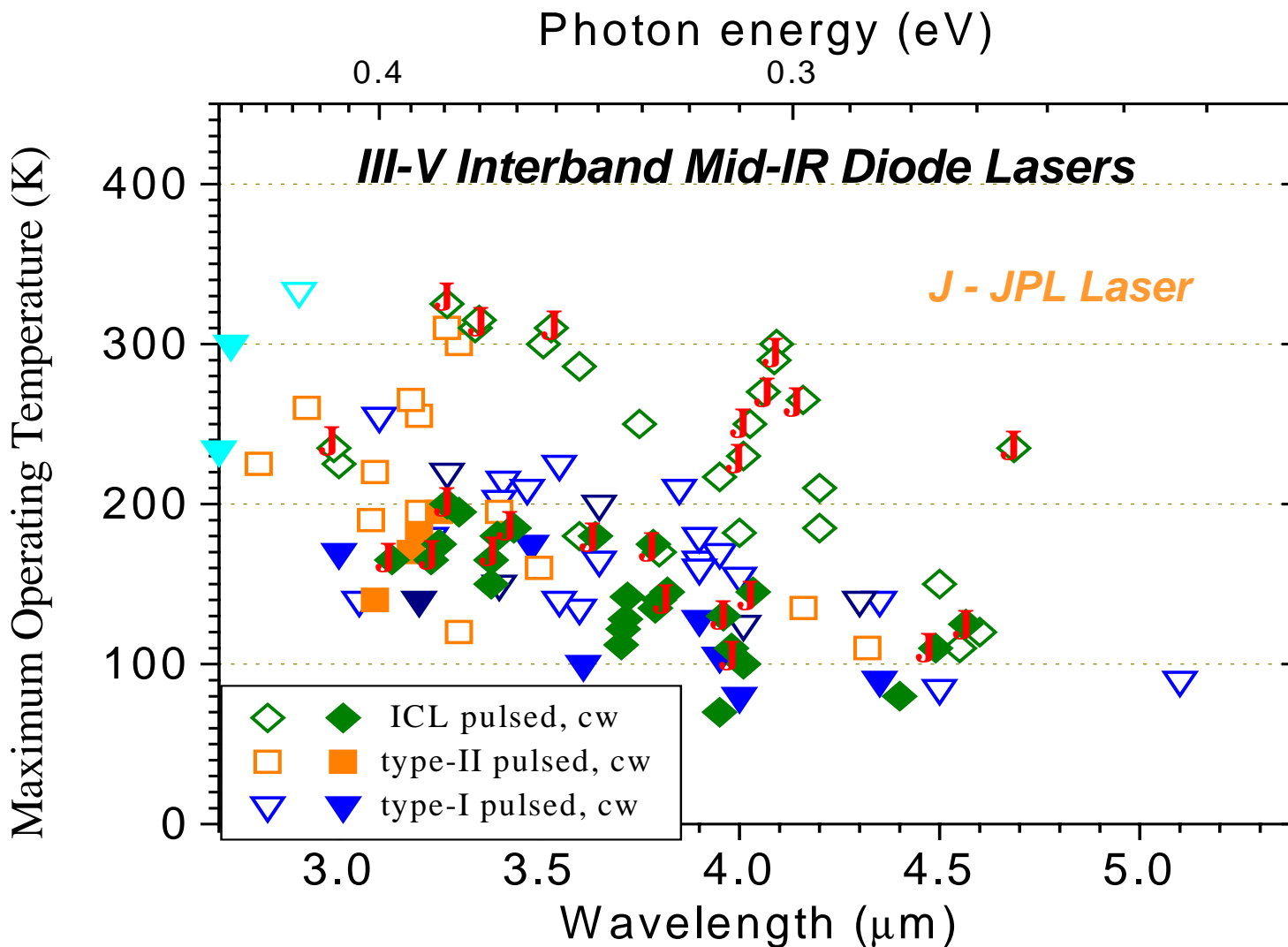
Related Maxion results:

At 80 K: $\eta_{wall} = 23\%$, DEQE ≈ 1 W/A (532%)

cw $T_{max} = 214$ K



JPL ICL STATUS: T_{max} (Compared to literature data, as of 9/2003)

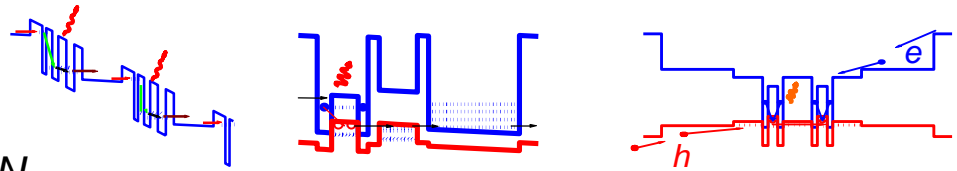




HEAT DISSIPATION REQUIREMENTS AT 300 K (QCL vs. W-ICL vs. W-Diode)

Current best:

- **QCL:** Current best cw threshold is $j_{th} \approx 1.9 \text{ kA/cm}^2$ (pulsed 1.2 kA/cm^2 reported), bias ($N = 30$ stages) is $V_{th} \approx 9 \text{ V}$ – Means $I_{dis} \approx 17 \text{ kW/cm}^2$ must be dissipated
- **ICL:** Best reported pulsed is $j_{th} \approx 1.05 \text{ kA/cm}^2$ at $V_{th} = 10.2 \text{ V}$ ($N = 15$) – Means $I_{dis} \approx 11 \text{ kW/cm}^2$
- **W-Diode:** For only pulsed 300 K result to date ($N_{QW} = 10$), $j_{th} \approx 16 \text{ kA/cm}^2$ at $V_{th} \approx 1.2 \text{ V}$ – Means $I_{dis} \approx 19 \text{ kW/cm}^2$



Scaling:

- **QCL:** j_{th} scales with loss; V_{th} scales with N
- **ICL:** j_{th} scales with Auger lifetime (τ_A), depends on loss; V_{th} scales with N
- **W-Diode:** j_{th} scales with N_{QW} & τ_A , depends on loss; Single-stage $V_{th} \approx \eta\omega$

Headroom:

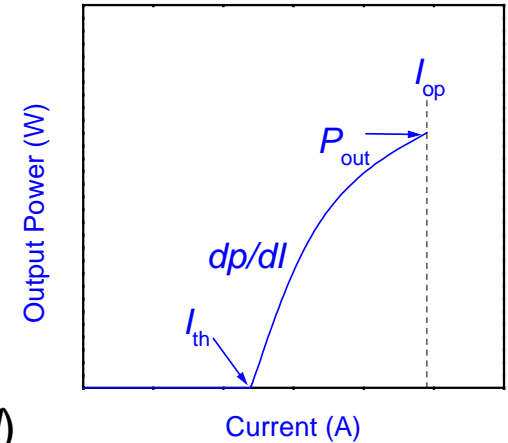
- **QCL:** How much further decrease of loss?; Decrease N to decrease V_{th} ? (So far, j_{th} then increases) [$I_{dis} \approx 8-10 \text{ kW/cm}^2$ probable – More?]
- **ICL (15-25 stages):** Much less mature so probably more headroom – Optimize V_{th} & possibly τ_A [$I_{dis} \approx 5-6 \text{ kW/cm}^2$ probable – More?]
- **W-Diode:** Very immature, so considerable headroom; $V_{th} \approx 0.5 \text{ V}$; Loss optimization may allow $N_{QW} = 3-5$ [$I_{dis} \approx 5 \text{ kW/cm}^2$ probable – More?]
- **Hybrid W-ICL with 3-5 stages (only enough to overcome loss):** Combines higher gain of ICL with lower V_{th} ($\approx 1.5-2.5 \text{ V}$) of W-Diode [Expect $I_{dis} < 3 \text{ kW/cm}^2$]



HIGH POWER: WHAT ABOUT ABOVE j_{th} ?

High-power laser must reach & exceed threshold, maintain large slope, minimize droop

- *Heat sinking*: InP overgrowth favors QCL, but gold plating may neutralize (Maxion ICL reports lowest R_{sp})
- *Higher T_0 of QCL*: Slower performance degradation for given ΔT
- Slope efficiency depends on loss & number of stages (N)
 - *Loss*: Thus far, lower in QCL ($\approx 10 \text{ cm}^{-1}$ vs. $\geq 20 \text{ cm}^{-1}$)
 - Advantage likely to persist because: (1) Fewer carriers, (2) No holes
 - *Slope efficiency*: Thus far, higher in QCL (e.g., 1 W/A for NU QCL @ 300 K vs. 0.42 W/A for Maxion ICL @ 200 K) – Immature ICL will improve
- *Broaden stripe*: Probably a necessity when scaling power up to $\geq 10 \text{ W}$ range
 - Precludes lateral heat flow, so low I_{dis} even more critical
 - Broad-stripe QCL (lower LEF) should maintain better beam quality
 - Photonic-Crystal DFB approach may improve both QCLs & ICLs





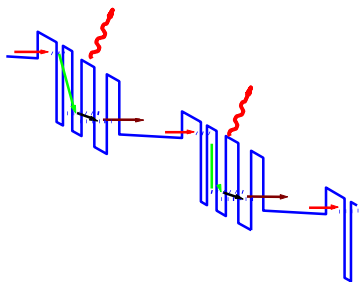
OTHER CONSIDERATIONS

- *Manufacturability:* InP-based materials growth/processing (QCLs) far more mature than GaSb-based (ICLs)
- *Wavelength coverage (Apples to oranges?):* Above analysis compares QCLs emitting at $\lambda \approx 6 \mu\text{m}$ to ICLs emitting at $\lambda \approx 3.5 \mu\text{m}$
 - Both get worse as they move toward the middle – Advantages will shift!
 - *One likely outcome:* QCLs will be advantageous at $\lambda > \lambda_{\text{Cross}}$ while ICLs advantageous at $\lambda < \lambda_{\text{Cross}}$ – Value of λ_{Cross} remains to be determined
- *Advantage also shifts with temperature:* Scenarios where QCLs are favored at $T \geq 300 \text{ K}$ may shift to ICLs with TE-cooling (e.g., 240 K)
 - *ICL in low-T limit:* $j_{\text{th}} = 9 \text{ A/cm}^2$

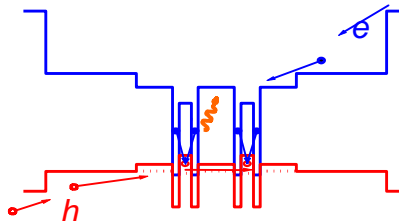


CONCLUSIONS

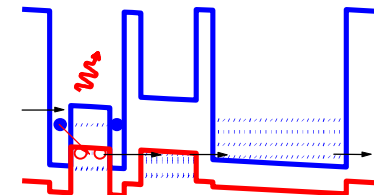
- Dramatic recent progress by both QCLs & ICLs
- High-power 3-5 μm CW lasing with electrical pumping at ambient (or TE-cooler) temperature seems increasingly likely
- ICL (or especially “hybrid” ICL) projected to require less power dissipation, but QCL has other advantages
- Jury still out on which will ultimately dominate under given λ & T constraints (Where is λ_{Cross} ?)



QCL



W-Diode



W-ICL